10656727 CLS

Most Frequently Occurring Classifications of Patents Returned From A Search of 10656727 on May 03, 2004

Original Classifications 4 250/504R 2 250/492.2 2 313/491 2 355/30 2 355/53 2 378/119 2 378/34 Cross-Reference Classifications

- 4 250/493.1
- 3 250/492.2
- 3 313/574
- 3 355/67
- 2 257/E21.035
- 2 257/E21.279
- 2 313/618
- 2 313/632
- 2 378/119

Combined Classifications

- 5 250/492.2
- 5 250/493.1
- 5 250/504R
- 4 378/119
- 3 313/491
- 3 313/574
- 3 313/632
- 355/53
- 355/67
- 378/34
- 250/574
- 257/E21.035
- 257/E21.279
- 313/618
- 355/30 2
- 356/338

10656727 CLSTITLES

Titles of Most Frequently Occurring Classifications of Patents Returne d

From A Search of 10656727 on May 03, 2004

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5 250/492.2 (2 OR, 3 XR)
       Class 250: RADIANT ENERGY
       250/492.1 IRRADIATION OF OBJECTS OR MATERIAL
       250/492.2 .Irradiation of semiconductor devices
5 250/493.1 (1 OR, 4 XR)
       Class 250: RADIANT ENERGY
       250/493.1 RADIANT ENERGY GENERATION AND SOURCES
5 250/504R (4 OR, 1 XR)
       Class 250: RADIANT ENERGY
       250/493.1 RADIANT ENERGY GENERATION AND SOURCES
       250/503.1 .With radiation modifying member
       250/504R
                    .. Ultraviolet or infrared source
4 378/119 (2 OR, 2 XR)
       Class 378: X-RAY OR GAMMA RAY SYSTEMS OR DEVICES
       378/119 SOURCE
3 313/491
              (2 OR, 1 XR)
              313 : ELECTRIC LAMP AND DISCHARGE DEVICES
       Class
       313/483
                    WITH LUMINESCENT SOLID OR LIQUID MATERIAL
       313/484
                    .With gaseous discharge medium
       313/485
                    .. Phosphor on envelope wall
       313/491
                    ... Electrode structure or material
3 313/574
               (0 \text{ OR}, 3 \text{ XR})
              313 : ELECTRIC LAMP AND DISCHARGE DEVICES
       Class
       313/567
                    WITH GAS OR VAPOR
                    .Having a particular total or partial pressure
       313/568
       313/572
                    .. One torr thru 760 torr
       313/574
                    ...With electrode structure
3 313/632 (1 OR, 2 XR)
       Class 313: ELECTRIC LAMP AND DISCHARGE DEVICES
       313/567
                    WITH GAS OR VAPOR
       313/631
                    .Having particular electrode structure
       313/632
                    .. Cathode or anode
3 355/53
              (2 OR, 1 XR)
       Class 355: PHOTOCOPYING
       355/18
                    PROJECTION PRINTING AND COPYING CAMERAS
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10656727 CLSTITLES 355/53 .Step and repeat 3 355/67 (0 OR, 3 XR) Class 355: PHOTOCOPYING 355/18 PROJECTION PRINTING AND COPYING CAMERAS 355/67 .Illumination systems or details 3 378/34 (2 OR, 1 XR) Class 378: X-RAY OR GAMMA RAY SYSTEMS OR DEVICES 378/1 SPECIFIC APPLICATION 378/34 .Lithography (1 OR, 1 XR)2 250/574 250 : RADIANT ENERGY Class 250/200 PHOTOCELLS; CIRCUITS AND APPARATUS 250/216 .Optical or pre-photocell system 250/573 ...Fluent material in optical path 250/574 ... Scattered or reflected light 257/E21.035 (0 OR, 2 XR) 257 : ACTIVE SOLID-STATE DEVICES Class 257/E21.001 PROCESSES OR APPARATUS ADAPTED FOR MANUFACTURE OR TREATMENT OF SEMICONDUCTOR OR SOLID-STATE DEVICES OR OF PARTS THEREOF (EPO) 257/E21.002 .Manufacture or treatment of semiconductor device (EPO) 257/E21.023 .. Making mask on semicond uctor body for further photolithographic processing (EPO 257/E21.033 ... Comprising inorganic layer (EPO) Characterized by their composition, e.g., 257/E21.035 multilayer masks, materials (EPO) (0 OR, 2 XR) 2 257/E21.279 257 : ACTIVE SOLID-STATE DEVICES Class 257/E21.001 PROCESSES OR APPARATUS ADAPTED FOR MANUFACTURE OR TREATMENT OF SEMICONDUCTOR OR SOLID-STATE DEVICES OR OF PARTS THEREOF (EPO) 257/E21.002 .Manufacture or treatment of semiconductor device (EPO) .. Device having at least one potential-jump 257/E21.04 barrier or surface barrier, e.g., PN junction, depletion layer, carrier concentration layer

(EDO)		10656727_CLSTITLES
(EPO)	257/E21.085	Device having semiconductor body comprising Group IV elements or Group III-V co
mpounds w	ith or without	
(EPO)		impurities, e.g., doping materials
	257/E21.211	Treatment of semiconductor body using process other than deposition of sem
iconducto	r material on	
f impurit	y material, or	a substrate, diffusion or alloying o
	257/E21.214	radiation treatment (EPO)To change their surface-physical characteristics or shape, e.g., etchi
ng, polis	hing, cutting	(EPO)
	257/E21.24	To form insulating layer thereon, e.g.,
hic techn	ique (EPO)	for masking or by using photolithograp
	257/E21.266 257/E21.271	Inorganic layer (EPO)Composed of oxide or glassy oxide or oxide based glass (EPO)
	257/E21.274 257/E21.278 257/E21.279	Deposition from gas or vapor (EPO)Deposition of silicon oxide (EPO)On silicon body (EPO)
2 313/	Class 313 :	R, 2 XR) ELECTRIC LAMP AND DISCHARGE DEVICES WITH GAS OR VAPOR .Having hollow cathode
2 355/		R, 0 XR) PHOTOCOPYING PROJECTION PRINTING AND COPYING CAMERAS With temperature or foreign particle control
2 356/	·	R, 1 XR) OPTICS: MEASURING AND TESTING BY PARTICLE LIGHT SCATTERING .With photocell detection